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Vishay Semiconductors

Hyperfast Rectifier, 2 x 10 A FRED Pt®





TO-220 FULL-PAK

TO-220AB

Base common cathode 02 Common cathode 3 Anode Anode

Common 10 cathode 3 Anode Anode

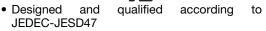
VS-20CTH03PbF VS-20CTH03-N3

VS-20CTH03FPPbF VS-20CTH03FP-N3

PRODUCT SUMMARY					
Package	TO-220AB, TO-220FP				
I _{F(AV)}	2 x 10 A				
V _R	300 V				
V _F at I _F	1.25 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Common cathode				

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending



 Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION/APPLICATIONS

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage		V _{RRM}		300	V	
	per diode	IF(AV)	T _C = 160 °C	10		
Average rectified forward current	(FULL-PAK) per diode		T _C = 135 °C		^	
	per device			20	A	
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	120		
Operating junction and storage temperatures		T _J , T _{Stg}		- 65 to 175	°C	

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN. TYP. MAX					
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	300	-	-			
Forward voltage	N/	I _F = 10 A	-	1.05	1.25	V		
	V _F	I _F = 10 A, T _J = 125 °C	-	0.85	0.95			
De sur la la sur sur st		V _R = V _R rated	-	-	20			
Reverse leakage current I _R		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	6	200	μA		
Junction capacitance	CT	V _R = 300 V	-	30	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH		

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Document Number: 94010

Pb-free

RoHS COMPLIANT HALOGEN FREE

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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	35		
	+	I _F = 1 A, dI _F /dt = 100 A/µs, V _R = 30 V		-	-	30		
	t _{rr}	T _J = 25 °C	I _F = 10 A dI _F /dt = 200 A/μs V _R = 200 V	-	31	-	A nC	
		T _J = 125 °C		-	42	-		
Deals receivers ourrent		T _J = 25 °C		-	2.4	-		
Peak recovery current	I _{RRM}	T _J = 125 °C		-	5.6	-		
Reverse recovery charge	0	T _J = 25 °C		-	36	-		
	Q_{rr} $T_J = 125^{\circ}$	T _J = 125 °C		-	120	-		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDTIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		- 65	-	175	°C	
Thermal resistance,	per diode		Mounting surface, flat, smooth	-	-	1.5	°C/W	
junction to case	(FULL-PAK) per diode	R _{thJC} and greased	-	-	3.9	0,11		
Marking device		Case style TO-220AB Case style TO-220 FULL-PAK		20CTH03				
				20CTH03FP				

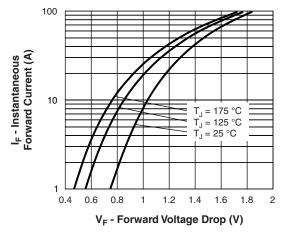


Fig. 1 - Typical Forward Voltage Drop Characteristics

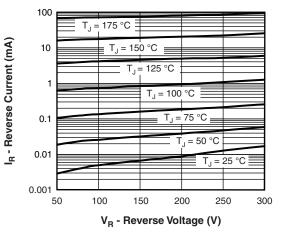


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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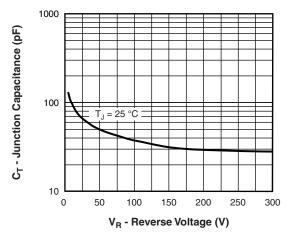


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

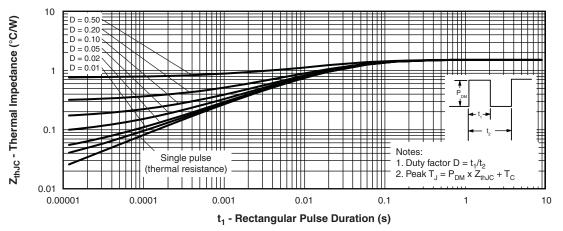


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

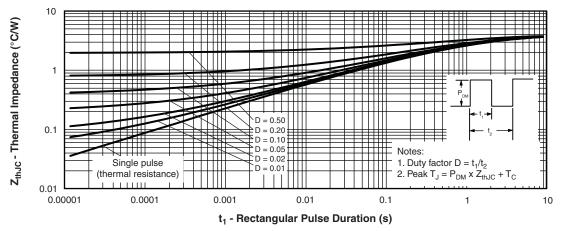
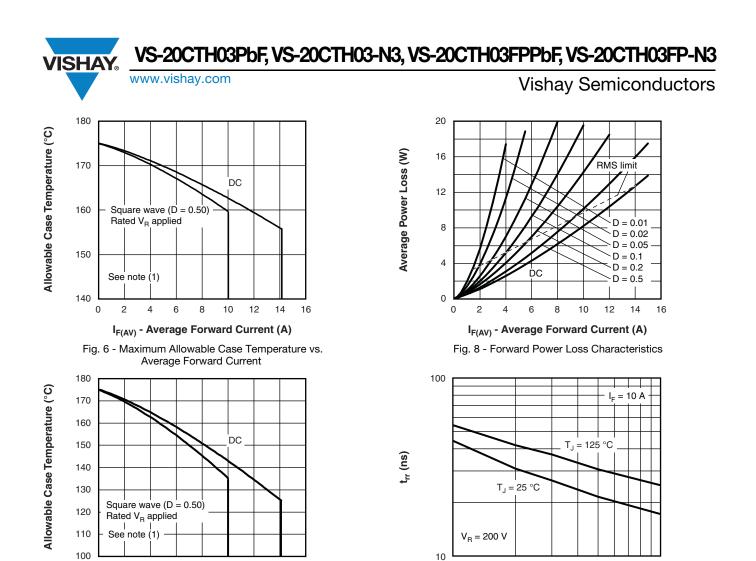


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)



dl_F/dt (A/µs)

100



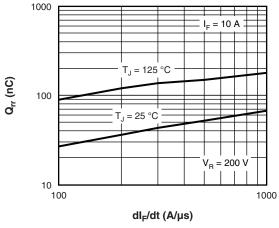


Fig. 10 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 8); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = Rated V_R

8

I_{F(AV)} - Average Forward Current (A)

Fig. 7 - Maximum Allowable Case Temperature vs.

Average Forward Current (FULL-PAK)

12

14 16

10

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0

2

4 6

4

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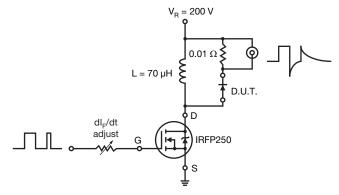
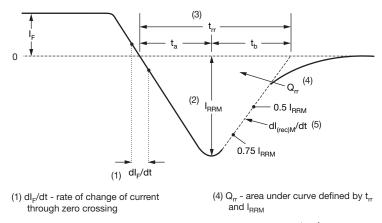
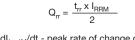


Fig. 11 - Reverse Recovery Parameter Test Circuit



(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.



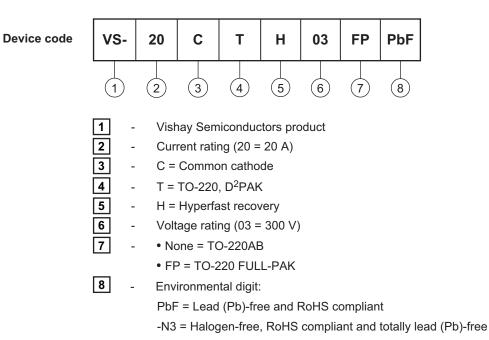
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

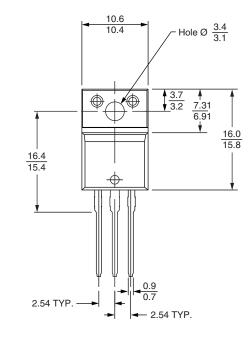


ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-20CTH03PbF	50	1000	Antistatic plastic tube			
VS-20CTH03-N3	50	1000	Antistatic plastic tube			
VS-20CTH03FPPbF	50	1000	Antistatic plastic tube			
VS-20CTH03FP-N3	50	1000	Antistatic plastic tube			

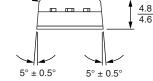
LINKS TO RELATED DOCUMENTS				
Dimensions	TO-220AB	www.vishay.com/doc?95222		
Dimensions	TO-220FP	www.vishay.com/doc?95072		
	TO-220ABPbF	www.vishay.com/doc?95225		
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028		
Part marking mornation	TO-220FPPbF	www.vishay.com/doc?95069		
	TO-220FP-N3	www.vishay.com/doc?95456		



DIMENSIONS in millimeters

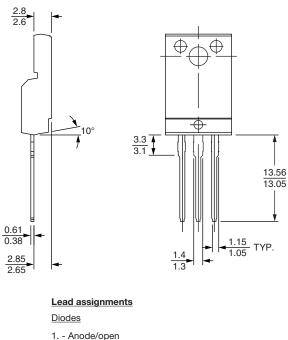


R 0.7 R 0.5 (2 places)





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2. - Cathode

3. - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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